



## 2N120

Power MOSFET

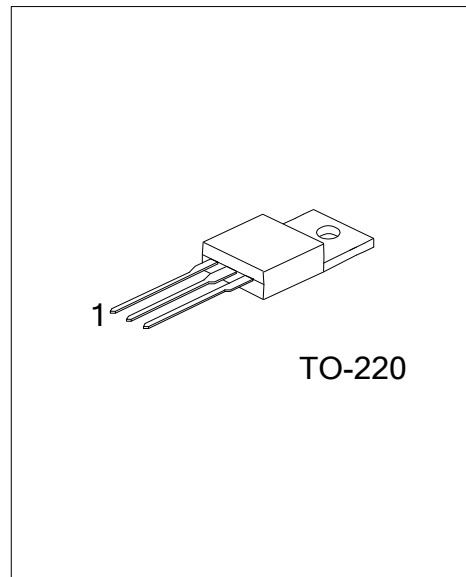
### 2A, 1200V N-CHANNEL POWER MOSFET

#### DESCRIPTION

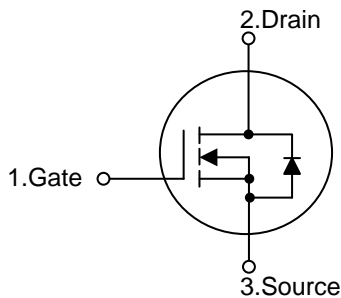
The UTC 2N120 provide excellent  $R_{DS(ON)}$ , low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

#### FEATURES

- \*  $R_{DS(ON)} \leq 7.5\Omega @ V_{GS}=10V, I_D=1.0A$
- \* Low Reverse Transfer Capacitance
- \* Fast Switching Capability
- \* Avalanche Energy Specified
- \* Improved dv/dt Capability, High Ruggedness



#### SYMBOL



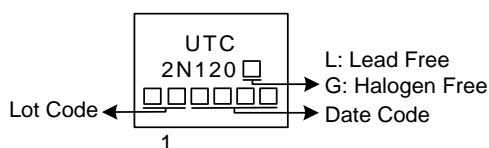
#### ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2N120L-TA3-T	2N120G-TA3-T	TO-220	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>2N120G-TA3-T</p> <p>(1) Packing Type</p> <p>(2) Package Type</p> <p>(3) Green Package</p>	<p>(1) T: Tube</p> <p>(2) TA3: TO-220</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
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#### MARKING



### ■ ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V <sub>DSS</sub>	1200	V
Gate-Source Voltage		V <sub>GSS</sub>	±30	V
Drain Current	Continuous	I <sub>D</sub>	2	A
	Pulsed (Note 2)	I <sub>DM</sub>	4	A
Avalanche Energy	Single Pulsed (Note 3)	E <sub>AS</sub>	473	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	3.1	V/ns
Power Dissipation		P <sub>D</sub>	75	W
Junction Temperature		T <sub>J</sub>	+150	°C
Storage Temperature		T <sub>STG</sub>	-55 ~ +150	°C

- Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.  
 2. Repetitive Rating : Pulse width limited by maximum junction temperature.  
 3. L=155mH, I<sub>AS</sub>=2.47A, V<sub>DD</sub>=90V, R<sub>G</sub>=25 Ω, Starting T<sub>J</sub> = 25°C  
 4. I<sub>SD</sub>≤2.0A, di/dt≤200A/μs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, Starting T<sub>J</sub> = 25°C

### ■ THERMAL CHARACTERISTICS

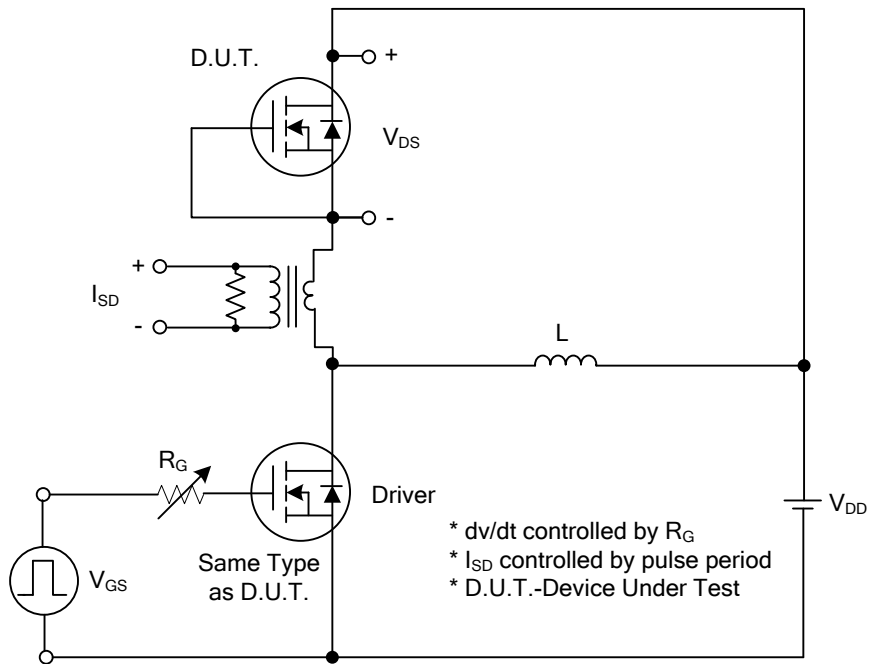
PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ <sub>JA</sub>	62.5	°C/W
Junction to Case	θ <sub>JC</sub>	1.79	°C/W

### ■ ELECTRICAL CHARACTERISTICS (T<sub>J</sub> =25°C, unless otherwise specified)

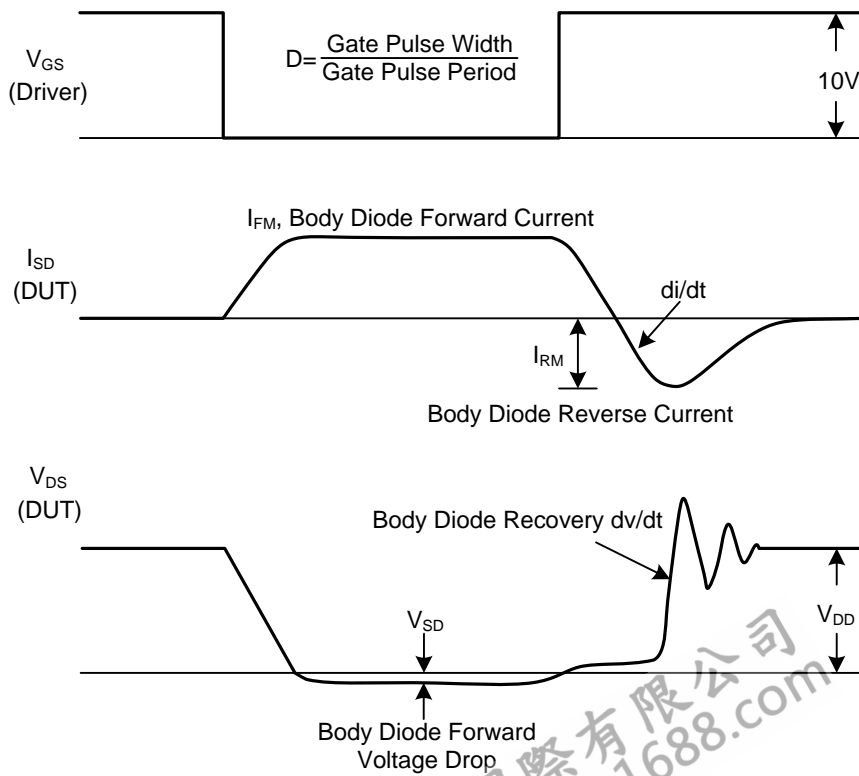
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	1200			V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =1200V, V <sub>GS</sub> =0V			10	μA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±30V, V <sub>DS</sub> =0V			±100	nA
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	3.0		5.0	V
Static Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =1.0A			7.5	Ω
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz		740		pF
Output Capacitance	C <sub>OSS</sub>			60		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			11		pF
<b>SWITCHING CHARACTERISTICS</b>						
Total Gate Charge (Note 1)	Q <sub>G</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =10V, I <sub>D</sub> =2A I <sub>G</sub> =1mA (Note 1, 2)		23		nC
Gate-Source Charge	Q <sub>GS</sub>			8		nC
Gate-Drain Charge	Q <sub>GD</sub>			8.5		nC
Turn-On Delay Time (Note 1)	t <sub>D(ON)</sub>	V <sub>DD</sub> =100V, V <sub>GS</sub> =10V, I <sub>D</sub> =2A, R <sub>G</sub> =25Ω (Note 1, 2)		24		ns
Turn-On Rise Time	t <sub>r</sub>			30		ns
Turn-Off Delay Time	t <sub>D(OFF)</sub>			64		ns
Turn-Off Fall Time	t <sub>f</sub>			48		ns
<b>SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS</b>						
Maximum Continuous Drain-Source Diode Forward Current	I <sub>S</sub>				2	A
Maximum Pulsed Drain-Source Diode Forward Current	I <sub>SM</sub>				4	A
Drain-Source Diode Forward Voltage (Note 1)	V <sub>SD</sub>	I <sub>S</sub> =2.0A, V <sub>GS</sub> =0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t <sub>rr</sub>	I <sub>S</sub> =2.0A, V <sub>GS</sub> =0V,		640		nS
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	di/dt=100A/μs		6.1		μC

- Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.  
 2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

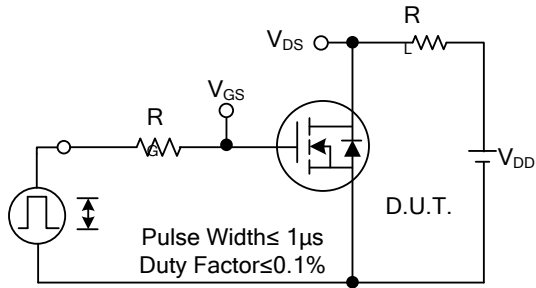


Peak Diode Recovery  $dv/dt$  Test Circuit

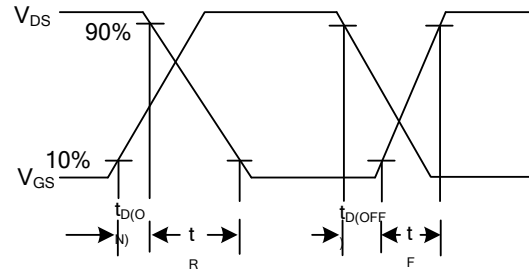


Peak Diode Recovery  $dv/dt$  Waveforms

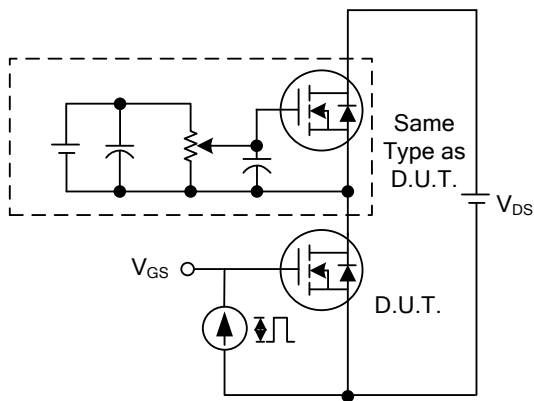
## TEST CIRCUITS AND WAVEFORMS



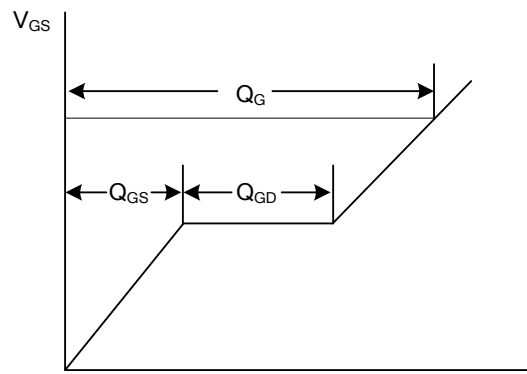
Switching Test Circuit



Switching Waveforms

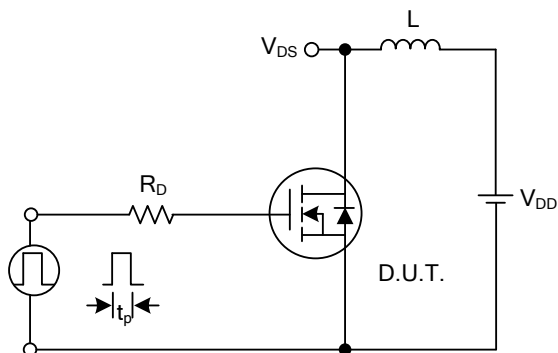


Gate Charge Test Circuit

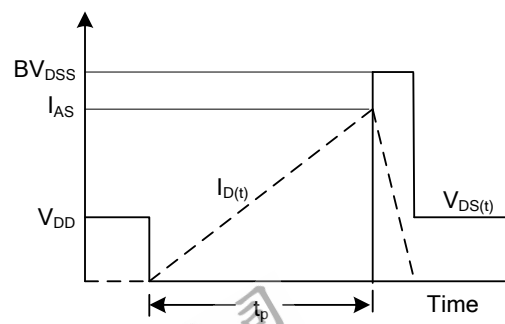


Charge

Gate Charge Waveform

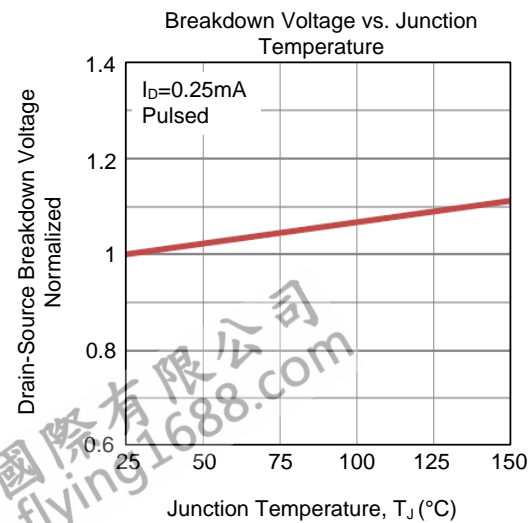
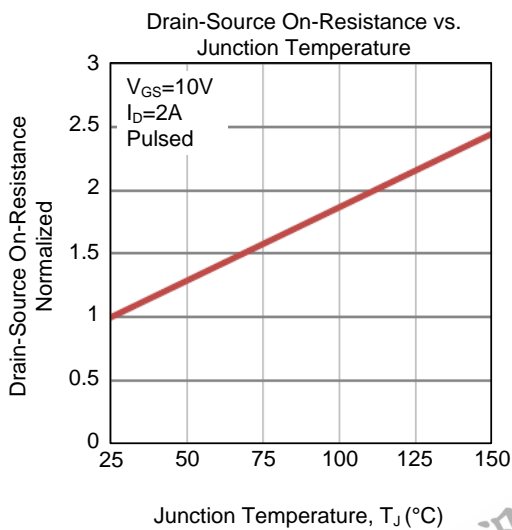
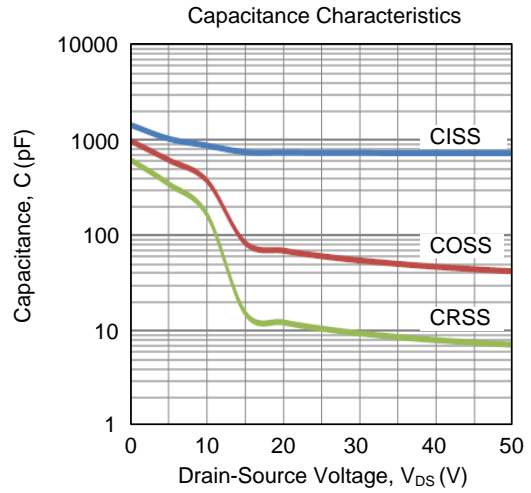
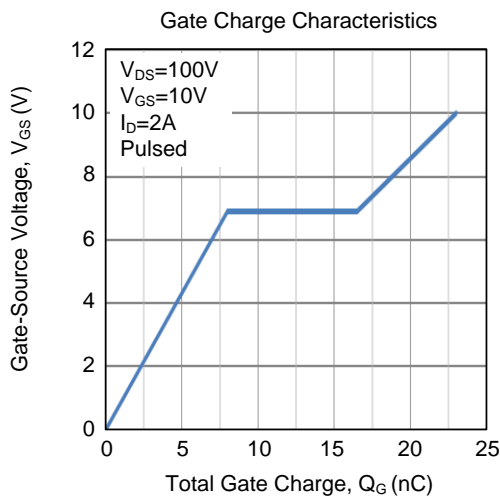
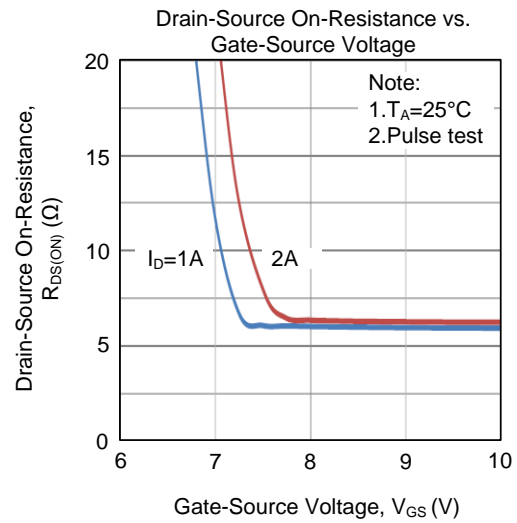
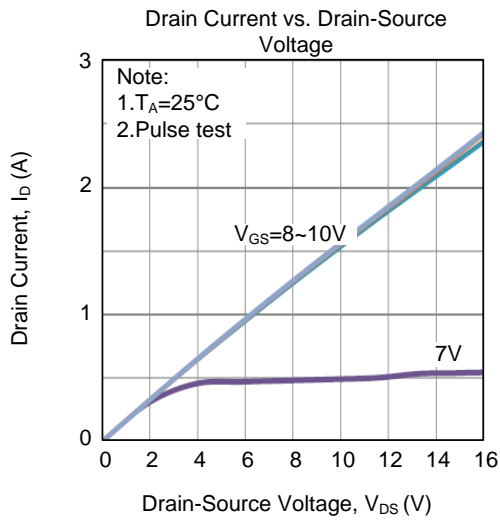


Unclamped Inductive Switching Test Circuit

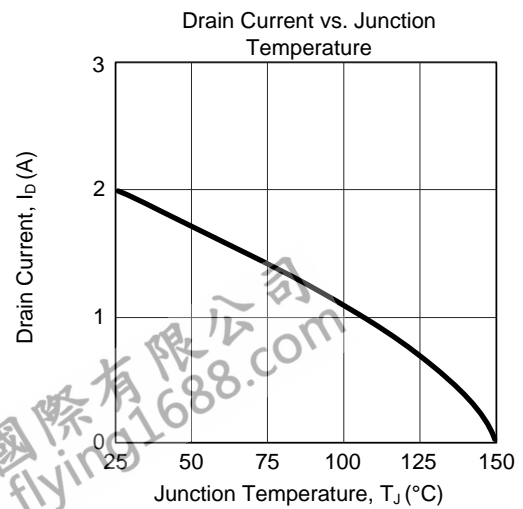
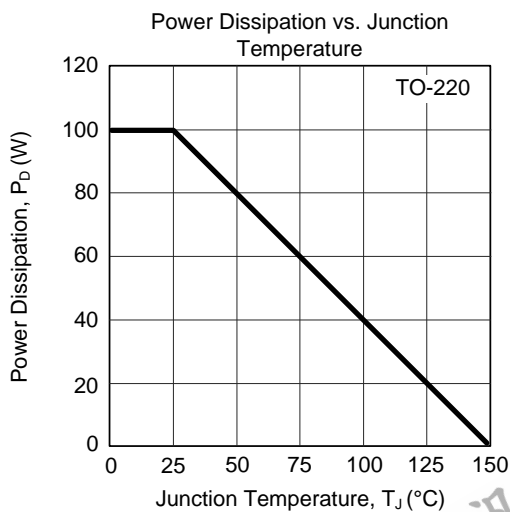
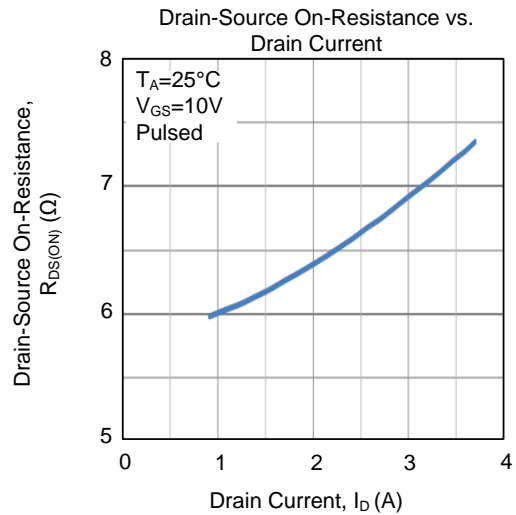
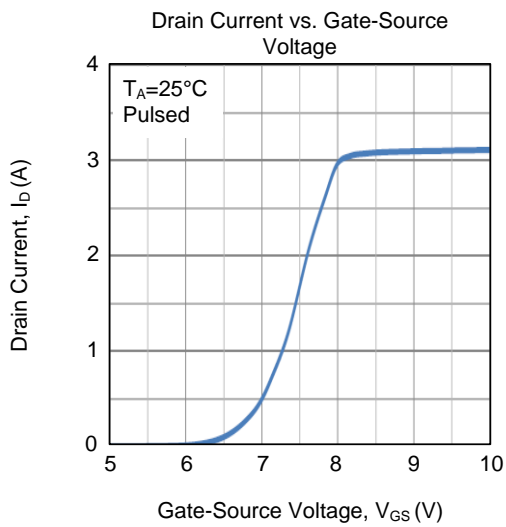
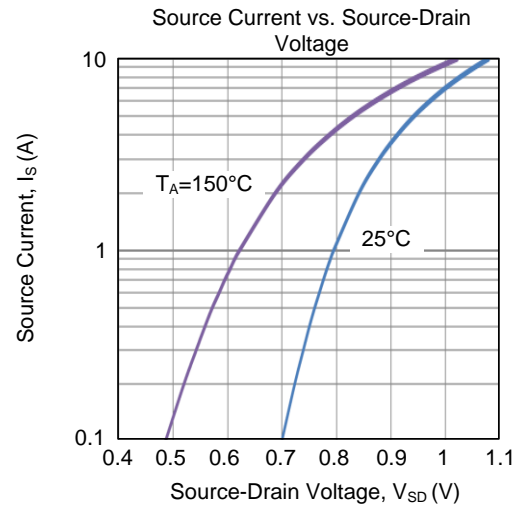
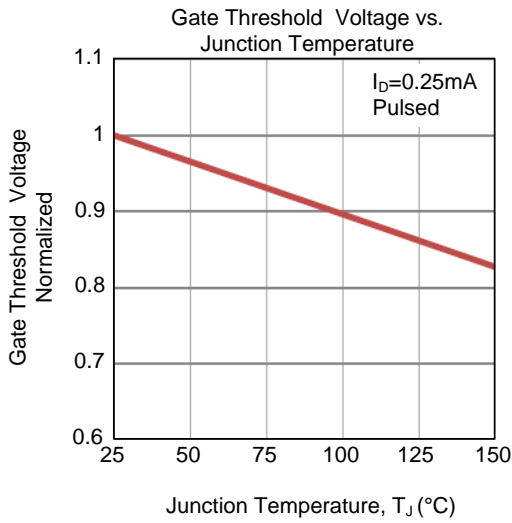


Unclamped Inductive Switching Waveforms

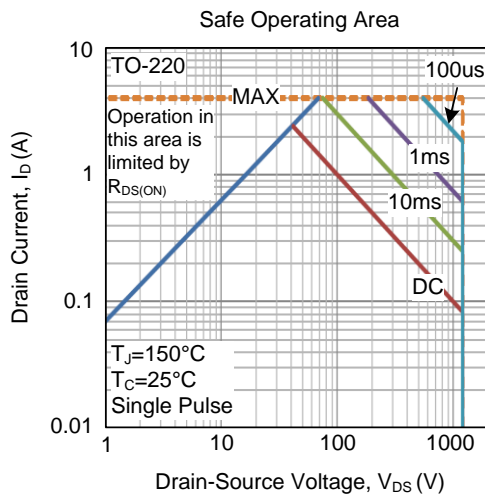
## TYPICAL CHARACTERISTICS



## ■ TYPICAL CHARACTERISTICS (Cont.)



■ **TYPICAL CHARACTERISTICS (Cont.)**



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